

Emitter customization code

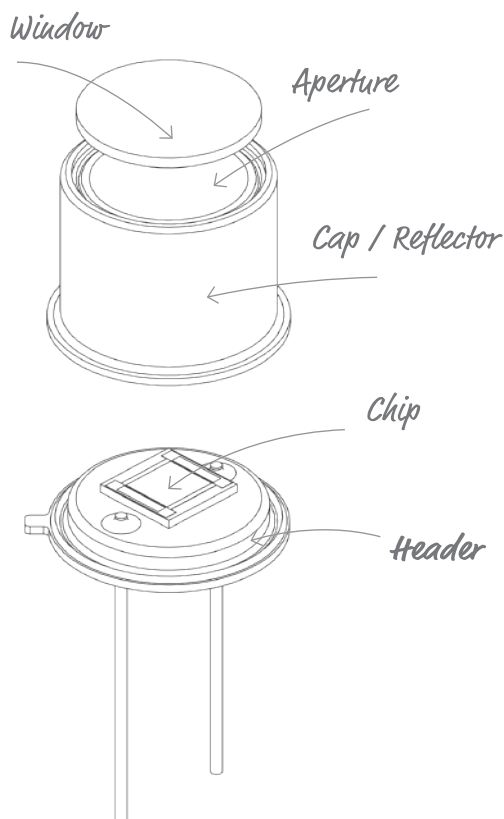
Thin film radiation sources

With this numerical code you can easily choose the right combination of source parts according to your application demands.

JSIRAAA-B-CC-D-EEE-F-GG-III

➤ For example

JSIR350-4-AL-C-D3.7-1-A7-I-AO



Thin film radiation source

JSIRAAA-B-

JSIR350-4-AL-C-D3.7-1-A7-I-AO

Thin film radiation source with chip type

JSIR 350-4 – NAC active area 2.2 x 2.2 mm²

JSIR 350-5 – NAC active area 0.65 x 0.65 mm²

JSIR 360-4 – Black-silicon active area 2.2 x 2.2 mm²

CC-

JSIR350-4-AL-C-D3.7-1-A7-I-AO

Header

AL – T039 (symmetric pin layout)

AI – T039 (assymetric pin layout)

BL – T046 (for chip type 5)

CB – SMD housing (for chip type 4)

CS – SMD housing (for chip type 5)

DL – T0 8

XX – Customized housing or packaging

D-

JSIR350-4-AL-C-D3.7-1-A7-I-AO

Cap

C – Cap

R – Reflector

0 – Without cap / reflector or SMD

EEE-

JSIR350-4-AL-C-D3.7-1-A7-I-AO

Aperture / cap / reflector type

S5.0 – Square 5 x 5 mm² (only with body CB)

S2.8 – Square 2.8 x 2.8 mm² (only with body CS)

D2.4 – Diameter 2.4 mm (only with body BL)

D2.5 – Diameter 2.5 mm (only with body BL)

D3.6 – Diameter 3.6 mm (only with reflector BL)

D3.7 – Diameter 3.7 mm (only with body AL)

D5.8 – Diameter 5.8 mm (only with body AL)

D6.0 – Diameter 6 mm (only with reflector AL)

CX – Customized type

0 – Without cap / reflector

F-

JSIR350-4-AL-C-D3.7-1-A7-I-AO

Filling gas

1 – Nitrogen (N₂)

2 – Krypton (Kr)

X – Customized filling gas

0 – Open

GG-

JSIR350-4-AL-C-D3.7-1-A7-I-AO

Window

A1 – Sapphire (Al₂O₃)

A2 – Calcium fluoride (CaF₂)

A4 – Barium fluoride (BaF₂)

A7 – Silicon ARC 2.5-15.5

XX – Customized window

0 – Without

III

JSIR350-4-AL-C-D3.7-1-A7-I-AO

Options

I – HermeSEAL® (only with window A1 or A7)

AO – Cap and add-on reflector



Type	JSIR 350-4	JSIR 360-4
Time constant (modulation)	17 ms	28 ms
Lifetime	100000 h at 610 °C	100000 h at 590 °C
Membrane temperature	610 °C at 650 mW nominal power	590 °C at 650 mW nominal power

